



P-Channel Enhancement-Mode Vertical DMOS FET

Features

- ▶ Low threshold (-2.0V max.)
- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage

Applications

- ▶ Logic level interfaces - ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Battery operated systems
- ▶ Photo voltaic drives
- ▶ Analog switches
- ▶ General purpose line drivers
- ▶ Telecom switches

Ordering Information

| Part Number | Package Option | Packing |
|-----------------|----------------|-----------|
| TP2640LG-G | 8-Lead SOIC | 2500/Reel |
| TP2640N3-G | 3-Lead TO-92 | 1000/Bag |
| TP2640N3-G P002 | 3-Lead TO-92 | 2000/Reel |
| TP2640N3-G P003 | | |
| TP2640N3-G P005 | | |
| TP2640N3-G P013 | | |
| TP2640N3-G P014 | | |

-G denotes a lead (Pb)-free / RoHS compliant package.

Contact factory for Wafer / Die availability.

Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

Absolute Maximum Ratings

| Parameter | Value |
|-----------------------------------|-----------------------------------|
| Drain-to-source voltage | BV_{DSS} |
| Drain-to-gate voltage | BV_{DGS} |
| Gate-to-source voltage | $\pm 20V$ |
| Operating and storage temperature | $-55^{\circ}C$ to $+150^{\circ}C$ |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Typical Thermal Resistance

| Package | θ_{ja} |
|-------------|------------------|
| 8-Lead SOIC | $101^{\circ}C/W$ |
| TO-92 | $132^{\circ}C/W$ |

General Description

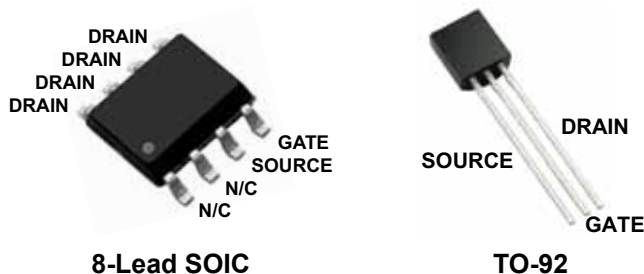
This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Product Summary

| BV_{DSS}/BV_{DGS} | $R_{DS(ON)}$ (max) | $I_{D(ON)}$ (min) | $V_{GS(th)}$ (max) |
|---------------------|-----------------------|----------------------|-----------------------|
| -400V | 15Ω | -2.0A | -0.7V |

Pin Configuration



Product Marking



YY = Year Sealed
WW = Week Sealed
L = Lot Number
_____ = "Green" Packaging

Package may or may not include the following marks: Si or

8-Lead SOIC



YY = Year Sealed
WW = Week Sealed
_____ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-92

Thermal Characteristics

| Package | I_D (continuous) [†] | I_D (pulsed) | Power Dissipation @ $T_A = 25^\circ\text{C}$ | I_{DR} [†] | I_{DRM} |
|-------------|------------------------------------|-------------------|---|-----------------------|-----------|
| 8-Lead SOIC | -86mA | -600mA | 0.74W [‡] | -86mA | -600mA |
| TO-92 | -180mA | -0.8mA | 1.0W | -180mA | -0.8mA |

[†] I_D (continuous) is limited by max rated T_J .

[‡] Mounted on FR5 board, 25mm x 25mm x 1.57mm.

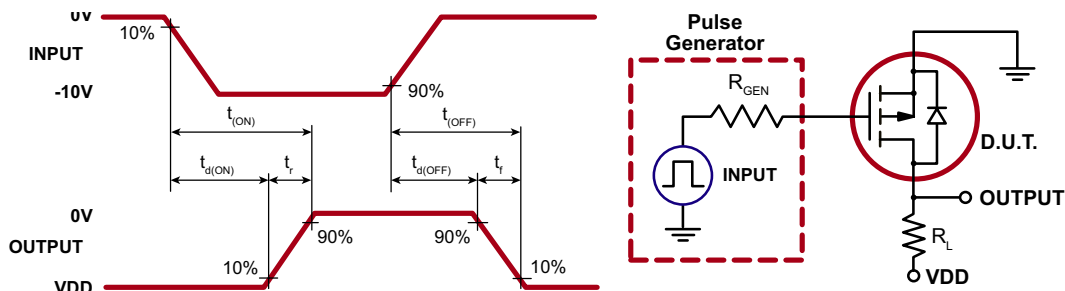
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Min | Typ | Max | Units | Conditions |
|---------------------|--|------|-----|-------|----------------------|---|
| BV_{DSS} | Drain-to-source breakdown voltage | -400 | - | - | V | $V_{GS} = 0V, I_D = -2.0mA$ |
| $V_{GS(th)}$ | Gate threshold voltage | -0.8 | - | -2.0 | V | $V_{GS} = V_{DS}, I_D = -1.0mA$ |
| $\Delta V_{GS(th)}$ | Change in $V_{GS(th)}$ with temperature | - | - | 5.0 | mV/ $^\circ\text{C}$ | $V_{GS} = V_{DS}, I_D = -1.0mA$ |
| I_{GSS} | Gate body leakage | - | - | -100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| I_{DSS} | Zero gate voltage drain current | - | - | -1.0 | μA | $V_{GS} = 0V, V_{DS} = -100V$ |
| | | | | -10.0 | μA | $V_{GS} = 0V, V_{DS} = \text{Max rating}$ |
| | | | | -1.0 | mA | $V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$ |
| $I_{D(ON)}$ | On-state drain current | -0.7 | - | - | A | $V_{GS} = -10V, V_{DS} = -25V$ |
| $R_{DS(ON)}$ | Static drain-to-source on-state resistance | - | 12 | 15 | Ω | $V_{GS} = -2.5V, I_D = -20mA$ |
| | | | 11 | 15 | | $V_{GS} = -4.5V, I_D = -150mA$ |
| | | | 11 | 15 | | $V_{GS} = -10V, I_D = -300mA$ |
| $\Delta R_{DS(ON)}$ | Change in $R_{DS(ON)}$ with temperature | - | - | 0.75 | %/ $^\circ\text{C}$ | $V_{GS} = -10V, I_D = -300mA$ |
| G_{FS} | Forward transconductance | 200 | - | - | mmho | $V_{DS} = -25V, I_D = -300mA$ |
| C_{ISS} | Input capacitance | - | - | 300 | pF | $V_{GS} = 0V,$ $V_{DS} = -25V,$ $f = 1.0MHz$ |
| C_{OSS} | Common source output capacitance | - | - | 50 | | |
| C_{RSS} | Reverse transfer capacitance | - | - | 12 | | |
| $t_{d(ON)}$ | Turn-on delay time | - | - | 10 | ns | $V_{DD} = -25V,$ $I_D = -300mA,$ $R_{GEN} = 25\Omega$ |
| t_r | Rise time | - | - | 15 | | |
| $t_{d(OFF)}$ | Turn-off delay time | - | - | 60 | | |
| t_f | Fall time | - | - | 40 | | |
| V_{SD} | Diode forward voltage drop | - | - | -1.8 | V | $V_{GS} = 0V, I_{SD} = -200mA$ |
| t_{rr} | Reverse recovery time | - | 300 | - | ns | $V_{GS} = 0V, I_{SD} = -200mA$ |

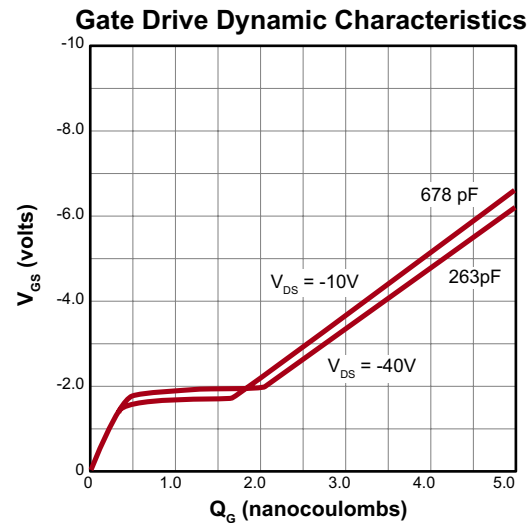
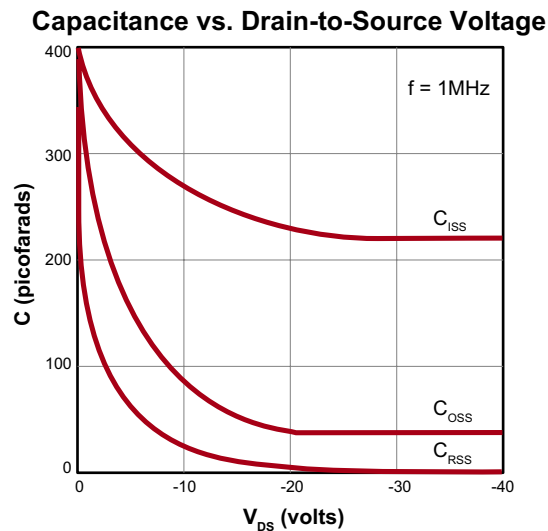
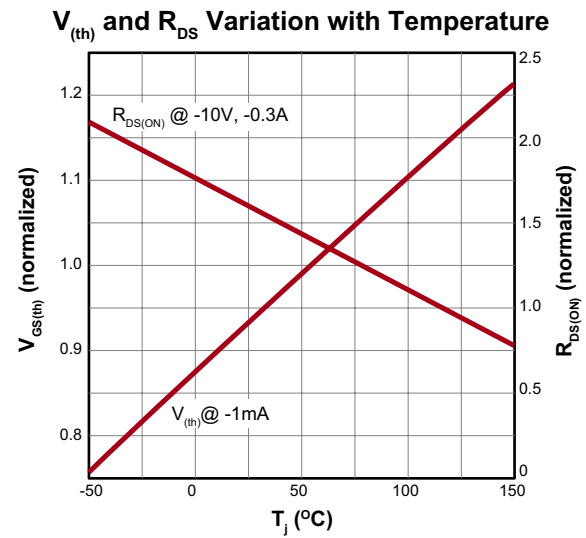
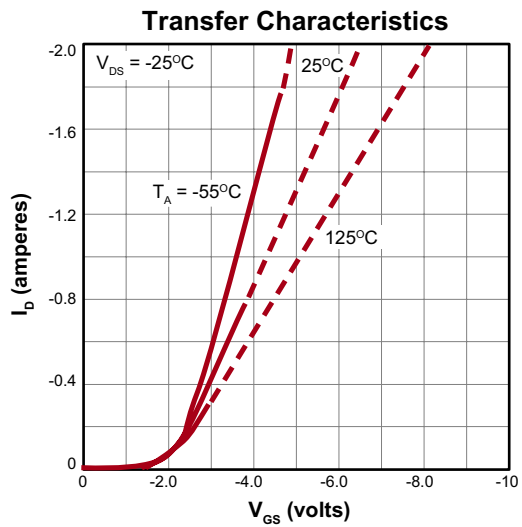
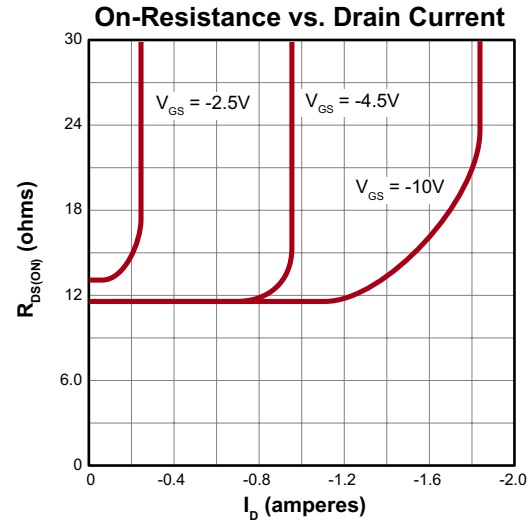
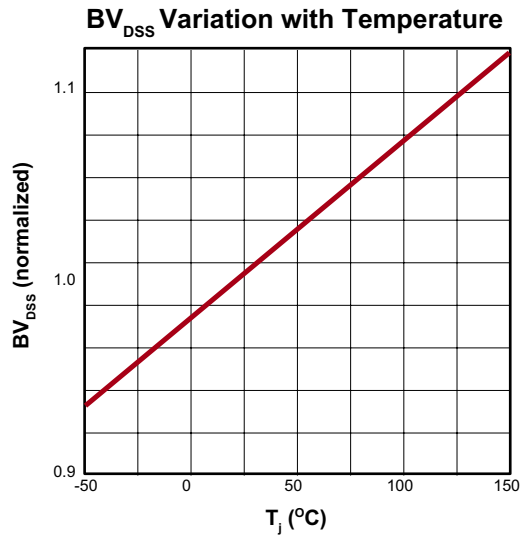
Notes:

1. All D.C. parameters 100% tested at 25C unless otherwise stated. (Pulse test: 300s pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

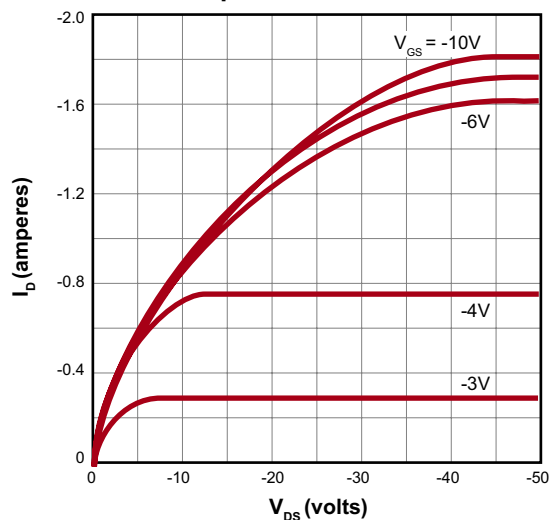


Typical Performance Curves

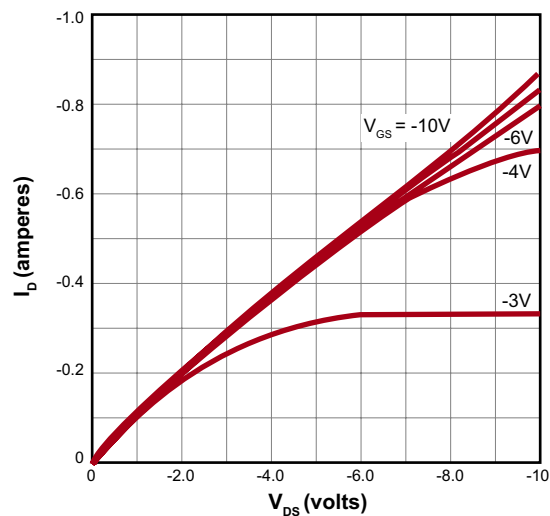


Typical Performance Curves (cont.)

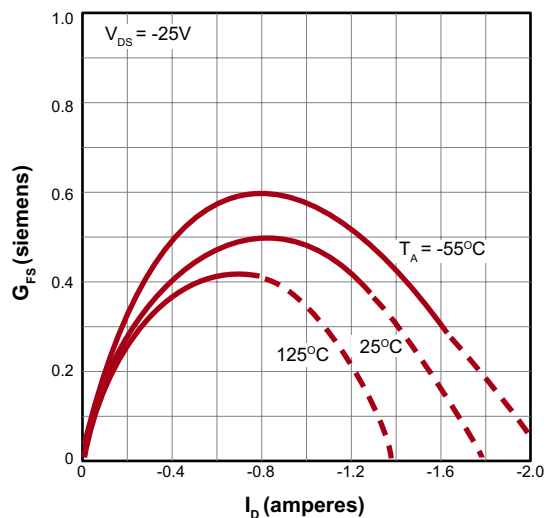
Output Characteristics



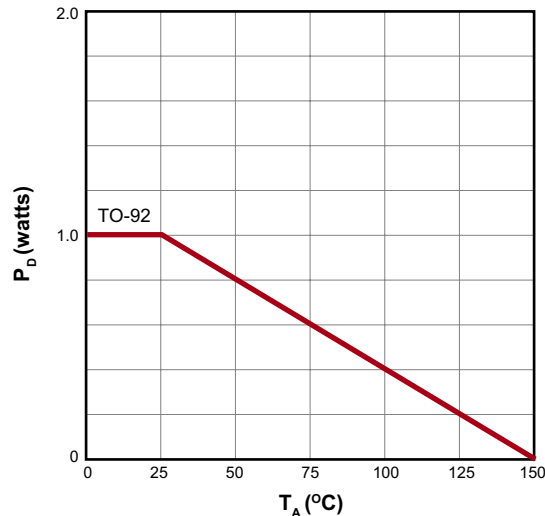
Saturation Characteristics



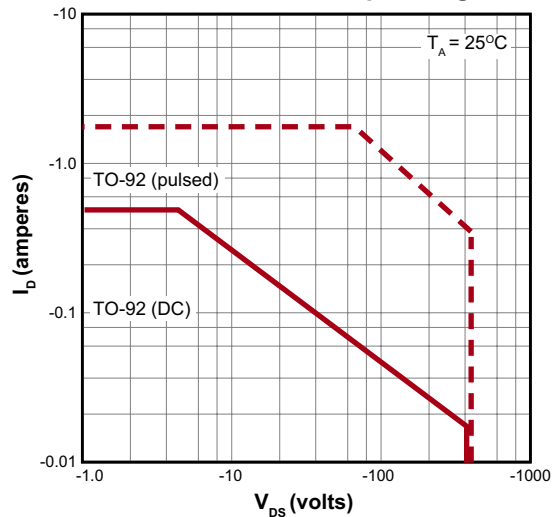
Transconductance vs. Drain Current



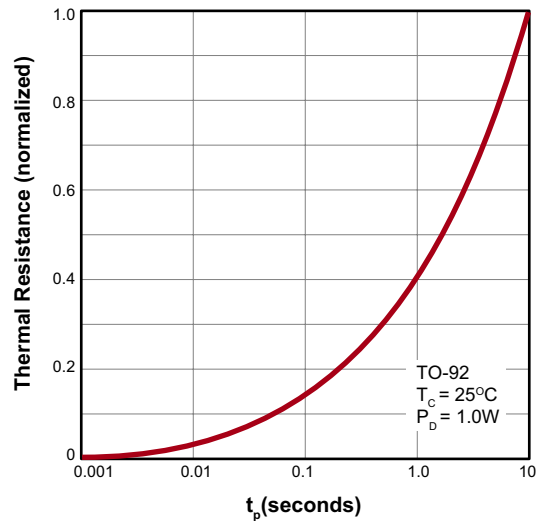
Power Dissipation vs. Temperature



Maximum Rated Safe Operating Area

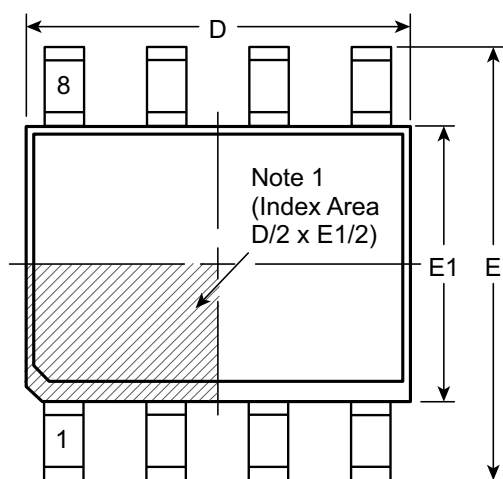


Thermal Response Characteristics

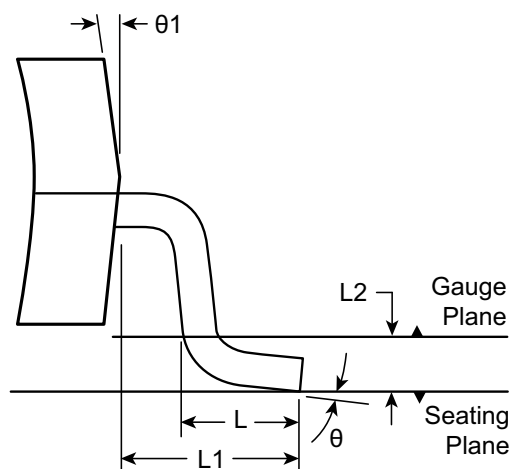


8-Lead SOIC (Narrow Body) Package Outline (LG)

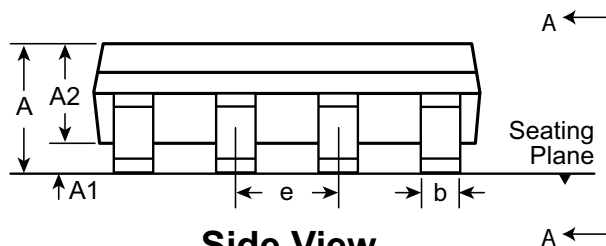
4.90x3.90mm body, 1.75mm height (max), 1.27mm pitch



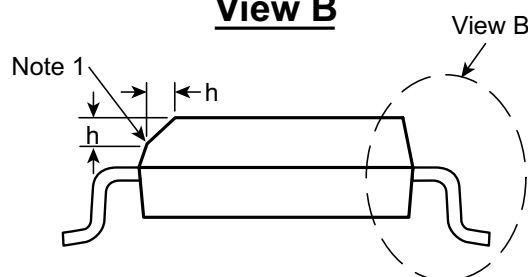
Top View



View B



Side View



View A-A

Note:

1. This chamfer feature is optional. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.

| Symbol | | A | A1 | A2 | b | D | E | E1 | e | h | L | L1 | L2 | θ | θ1 |
|-------------------|-----|-------|------|-------|------|-------|-------|-------|-------------|------|------|-------------|-------------|----|-----|
| Dimension (mm) | MIN | 1.35* | 0.10 | 1.25 | 0.31 | 4.80* | 5.80* | 3.80* | 1.27 BSC | 0.25 | 0.40 | 1.04 REF | 0.25 BSC | 0° | 5° |
| | NOM | - | - | - | - | 4.90 | 6.00 | 3.90 | | - | - | | | - | - |
| | MAX | 1.75 | 0.25 | 1.65* | 0.51 | 5.00* | 6.20* | 4.00* | | 0.50 | 1.27 | | | 8° | 15° |

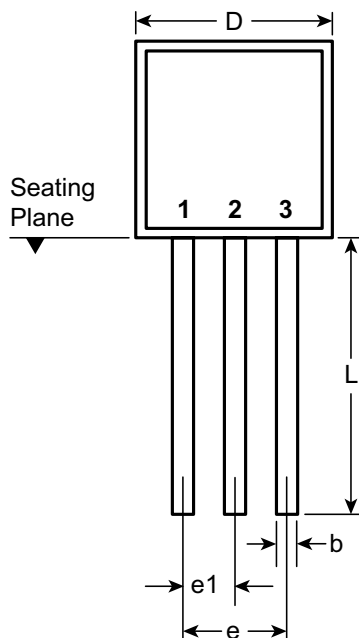
JEDEC Registration MS-012, Variation AA, Issue E, Sept. 2005.

* This dimension is not specified in the JEDEC drawing.

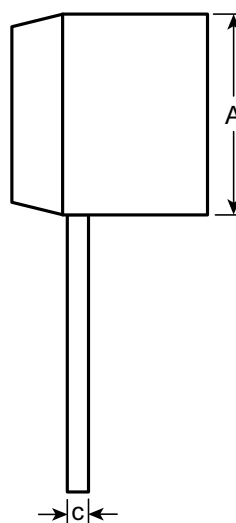
Drawings are not to scale.

Supertex Doc. #: DSPD-8SOLGTG, Version I041309.

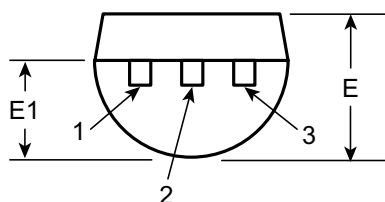
3-Lead TO-92 Package Outline (N3)



Front View



Side View



Bottom View

| Symbol | | A | b | c | D | E | E1 | e | e1 | L |
|------------------------|-----|------|-------------------|-------------------|------|------|------|------|------|-------|
| Dimensions (inches) | MIN | .170 | .014 [†] | .014 [†] | .175 | .125 | .080 | .095 | .045 | .500 |
| | NOM | - | - | - | - | - | - | - | - | - |
| | MAX | .210 | .022 [†] | .022 [†] | .205 | .165 | .105 | .105 | .055 | .610* |

JEDEC Registration TO-92.

* This dimension is not specified in the JEDEC drawing.

† This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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